

# **isc Silicon NPN Power Transistor**

#### **DESCRIPTION**

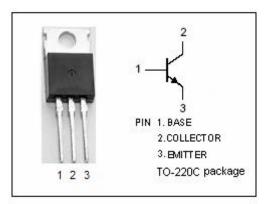
- · Low Collector Saturation Voltage
- : V<sub>CE(sat)</sub>= 1.0V(Max)@I<sub>C</sub>= 2A
- · Wide Area of Safe Operation
- · Complement to Type 2SB1064
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

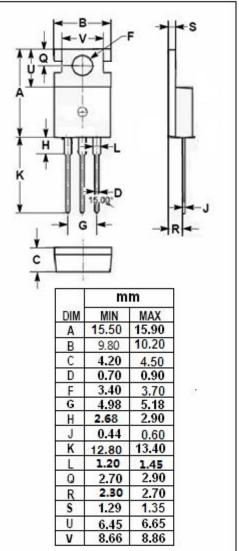
#### **APPLICATIONS**

• Designed for low frequency power amplifier applications.

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	60	V	
VCEO	Collector-Emitter Voltage	50	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	3	А	
I <sub>CM</sub>	Collector Current-Peak	4.5	А	
P <sub>C</sub>	Total Power Dissipation @ T <sub>a</sub> =25℃	1.5	W	
	Total Power Dissipation @ T <sub>C</sub> =25℃	30		
TJ	Junction Temperature 150		$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range -55~1		$^{\circ}$	







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2SD1505

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>B</sub> = 0	50			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 50 μ A; I <sub>E</sub> = 0	60			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 50 μ A; I <sub>C</sub> = 0	5			V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A			1.0	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 40V; I <sub>E</sub> = 0			1.0	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			1.0	μА
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 3V	60		320	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V		90		MHz
Сов	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = 10V; f= 1MHz		40		pF

## ♦ h<sub>FE</sub> Classifications

D	E	F
60-120	100-200	160-320

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